

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

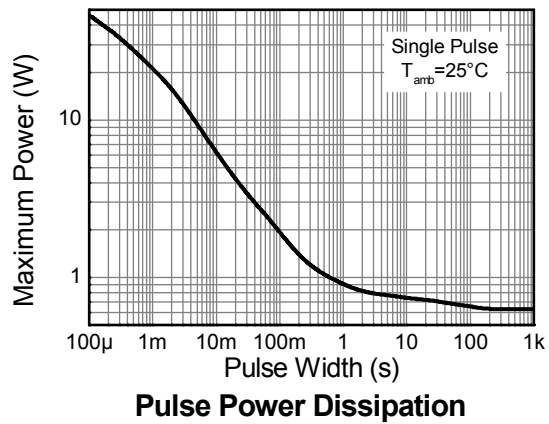
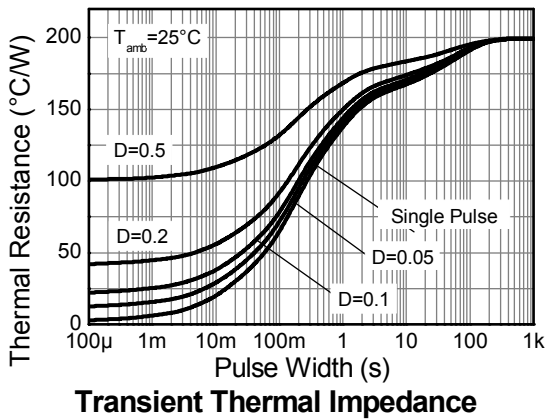
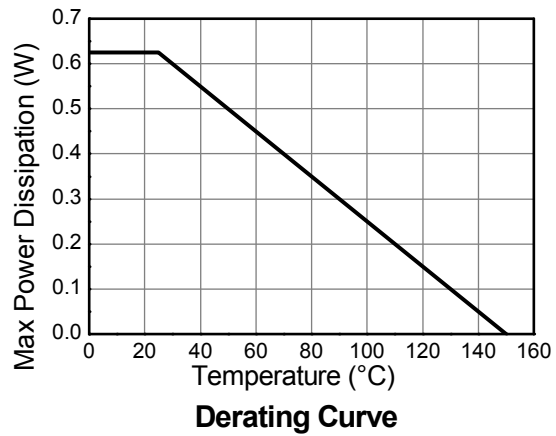
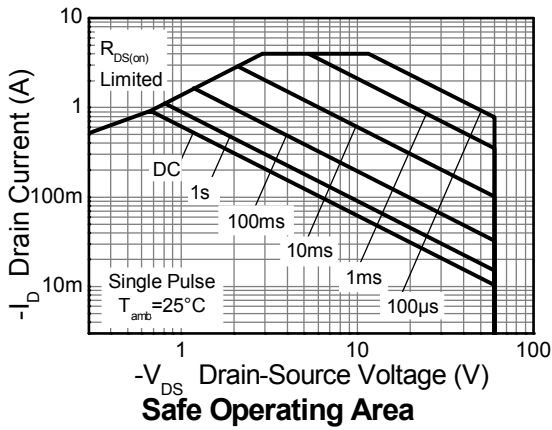
| Characteristic                                  |                        |                                    | Symbol    | Value        | Units |
|---|------------------------|------------------------------------|-----------|--------------|-------|
| Drain-Source Voltage                            |                        |                                    | $V_{DSS}$ | -60          | V     |
| Gate-Source Voltage                             |                        |                                    | $V_{GS}$  | $\pm 20$     | V     |
| Continuous Drain Current                        | $V_{GS} = -10\text{V}$ | $T_A = +70^\circ\text{C}$ (Note 7) | $I_D$     | -1.1         | A     |
|   |                        | (Note 7)<br>(Note 6)               |           | -0.8<br>-0.9 |       |
| Pulsed Drain Current (Note 7)                   |                        |                                    | $I_{DM}$  | -4           | A     |
| Continuous Source Current (Body Diode) (Note 6) |                        |                                    | $I_S$     | -1.2         | A     |
| Pulsed Source Current (Body Diode) (Note 7)     |                        |                                    | $I_{SM}$  | -4           | A     |

**Thermal Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

| Characteristic                                   |  | Symbol          | Value       | Unit                      |
|--|--|-----------------|-------------|---------------------------|
| Power Dissipation (Note 5)                       |  | $P_D$           | 625         | mW                        |
| Linear Derating Factor                           |  |                 | 5           | mW/ $^\circ\text{C}$      |
| Power Dissipation (Note 6)                       |  | $P_D$           | 806         | mW                        |
| Linear Derating Factor                           |  |                 | 6.5         | mW/ $^\circ\text{C}$      |
| Thermal Resistance, Junction to Ambient (Note 5) |  | $R_{\theta JA}$ | 200         | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction to Ambient (Note 6) |  | $R_{\theta JA}$ | 155         | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction to Leads (Note 8)   |  | $R_{\theta JL}$ | 194         | $^\circ\text{C}/\text{W}$ |
| Operating and Storage Temperature Range          |  | $T_J, T_{STG}$  | -55 to +150 | $^\circ\text{C}$          |

- Notes:
5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
  6. For a device surface mounted on FR4 PCB measured at  $t \leq 5\text{secs}$ .
  7. Repetitive rating 25mm x 25mm FR4 PCB,  $D = 0.05$  pulse width =  $10\mu\text{s}$  - pulse current limited by maximum junction temperature.
  8. Thermal resistance from junction to solder-point (at the end of the collector lead).

**Thermal Characteristics**

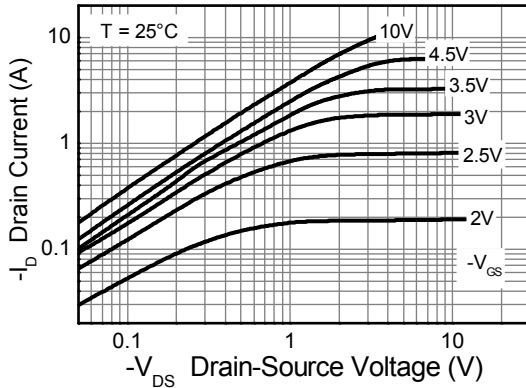


**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

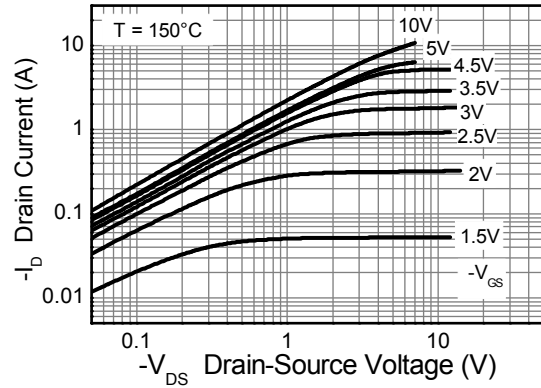
| Characteristic                             | Symbol              | Min | Typ   | Max   | Unit | Test Condition   |
|--|---------------------|-----|-------|-------|------|--|
| <b>OFF CHARACTERISTICS</b>                 |                     |     |       |       |      |  |
| Drain-Source Breakdown Voltage             | BV <sub>DSS</sub>   | -60 | —     | —     | V    | I <sub>D</sub> = -250μA, V <sub>GS</sub> = 0V  |
| Zero Gate Voltage Drain Current            | I <sub>DSS</sub>    | —   | —     | -0.5  | μA   | V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V   |
| Gate-Source Leakage                        | I <sub>GSS</sub>    | —   | —     | ±100  | nA   | V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V   |
| <b>ON CHARACTERISTICS</b>                  |                     |     |       |       |      |  |
| Gate Threshold Voltage                     | V <sub>GS(th)</sub> | -1  | —     | -3    | V    | I <sub>D</sub> = -250μA, V <sub>DS</sub> = V <sub>GS</sub>                                     |
| Static Drain-Source On-Resistance (Note 9) | R <sub>DS(on)</sub> | —   | —     | 0.400 | Ω    | V <sub>GS</sub> = -10V, I <sub>D</sub> = -0.9A   |
|  |                     |     |       | 0.600 |      | V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -0.8A  |
| Forward Transconductance (Notes 9 & 11)    | g <sub>fs</sub>     | —   | 1.8   | —     | S    | V <sub>DS</sub> = -15V, I <sub>D</sub> = -0.9A   |
| Diode Forward Voltage (Note 9)             | V <sub>SD</sub>     | —   | -0.85 | -0.95 | V    | T <sub>J</sub> = +25°C, I <sub>S</sub> = -0.8A, V <sub>GS</sub> = 0V                           |
| Reverse Recovery Time (Note 11)            | t <sub>rr</sub>     | —   | 21.1  | —     | ns   | T <sub>J</sub> = +25°C, I <sub>F</sub> = -0.9A,  |
| Reverse Recovery Charge (Note 11)          | Q <sub>rr</sub>     | —   | 19.3  | —     | nC   | di/dt = 100A/μs  |
| <b>DYNAMIC CHARACTERISTICS</b> (Note 11)   |                     |     |       |       |      |  |
| Input Capacitance                          | C <sub>iss</sub>    | —   | 219   | —     | pF   | V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V<br>f = 1MHz                                       |
| Output Capacitance                         | C <sub>oss</sub>    | —   | 25.7  | —     |      |  |
| Reverse Transfer Capacitance               | C <sub>rss</sub>    | —   | 20.5  | —     |      |  |
| Turn-On Delay Time (Note 10)               | t <sub>D(on)</sub>  | —   | 1.6   | —     | ns   | V <sub>DD</sub> = -30V, I <sub>D</sub> = -1A,<br>R <sub>G</sub> ≅ 6.0Ω, V <sub>GS</sub> = -10V |
| Turn-On Rise Time (Note 10)                | t <sub>r</sub>      | —   | 2.2   | —     |      |  |
| Turn-Off Delay Time (Note 10)              | t <sub>D(off)</sub> | —   | 11.2  | —     |      |  |
| Turn-Off Fall Time (Note 10)               | t <sub>f</sub>      | —   | 5.7   | —     |      |  |
| Total Gate Charge (Note 10)                | Q <sub>g</sub>      | —   | 2.9   | —     | nC   | V <sub>DS</sub> = -30V, V <sub>GS</sub> = -4.5V,<br>I <sub>D</sub> = -0.9A                     |
| Total Gate Charge (Note 10)                | Q <sub>g</sub>      | —   | 5.9   | —     | nC   | V <sub>DS</sub> = -30V, V <sub>GS</sub> = -10V,<br>I <sub>D</sub> = -0.9A                      |
| Gate-Source Charge (Note 10)               | Q <sub>gs</sub>     | —   | 0.74  | —     |      |  |
| Gate-Drain Charge (Note 10)                | Q <sub>gd</sub>     | —   | 1.5   | —     |      |  |

- Notes:
9. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤ 2%.
  10. Switching characteristics are independent of operating junction temperature.
  11. For design aid only, not subject to production testing.

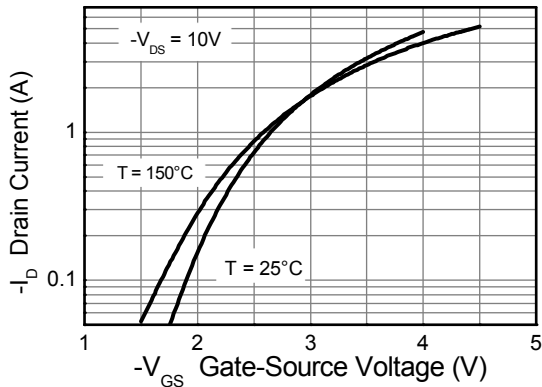
**Typical Characteristics**



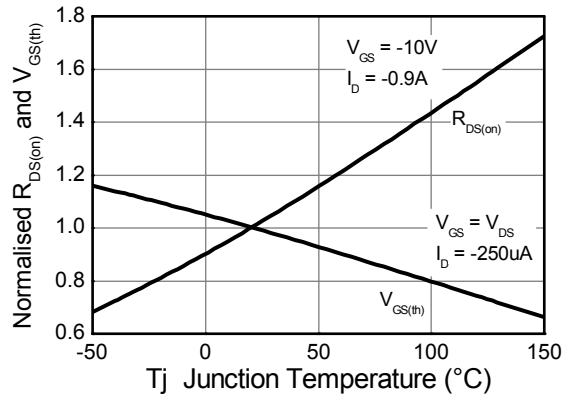
**Output Characteristics**



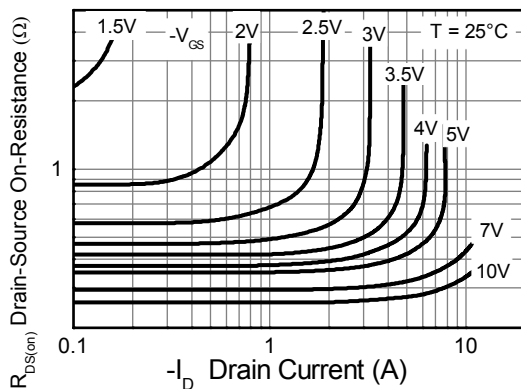
**Output Characteristics**



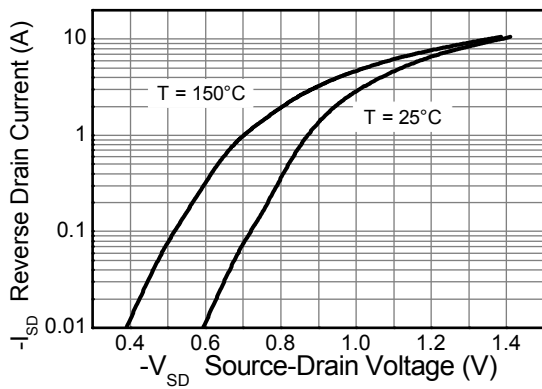
**Typical Transfer Characteristics**



**Normalised Curves v Temperature**

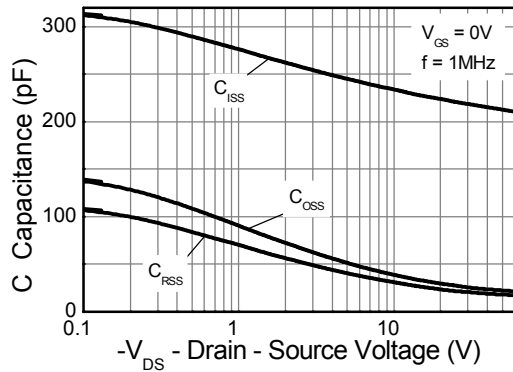


**On-Resistance v Drain Current**

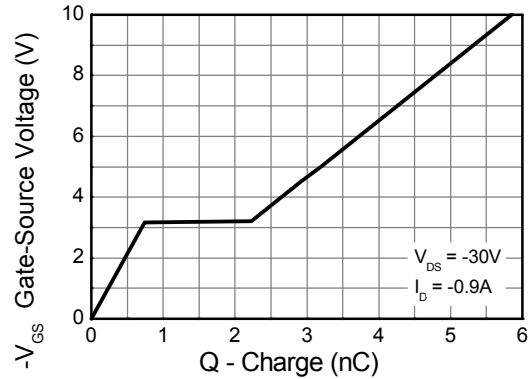


**Source-Drain Diode Forward Voltage**

**Typical Characteristics – (cont.)**

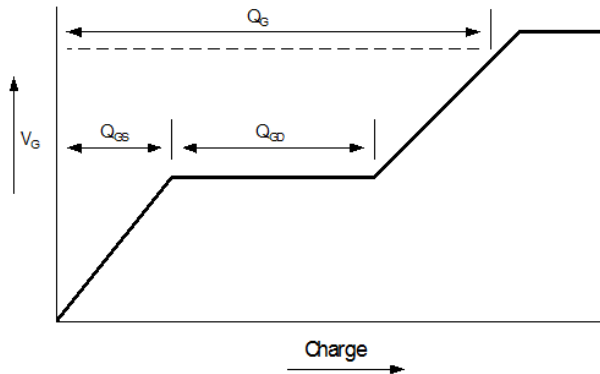


**Capacitance v Drain-Source Voltage**

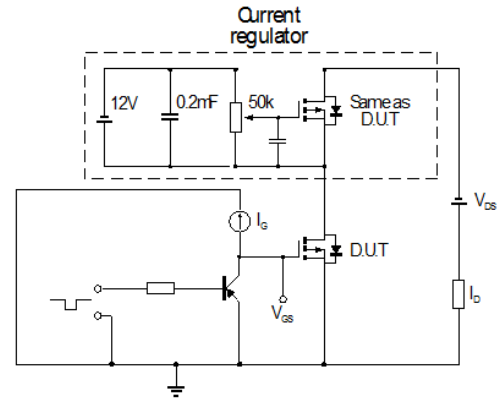


**Gate-Source Voltage v Gate Charge**

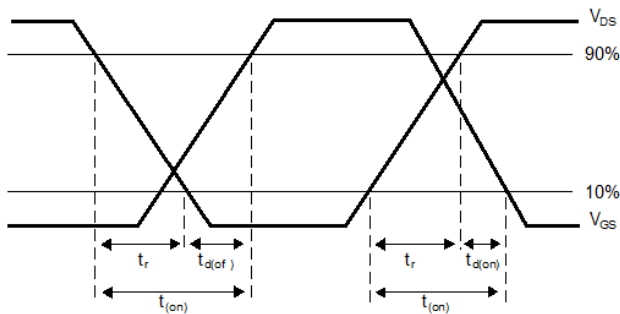
**Test Circuits**



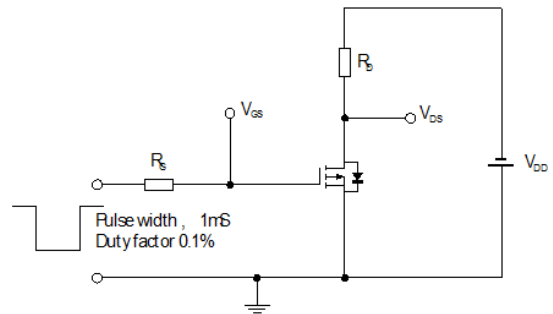
**Basic gate charge waveform**



**Gate charge test circuit**



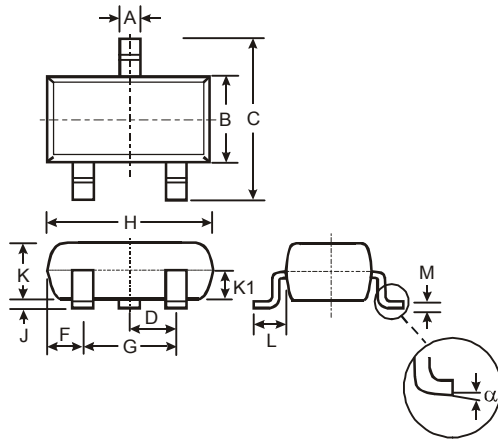
**Switching time waveforms**



**Switching time test circuit**

## Package Outline Dimensions

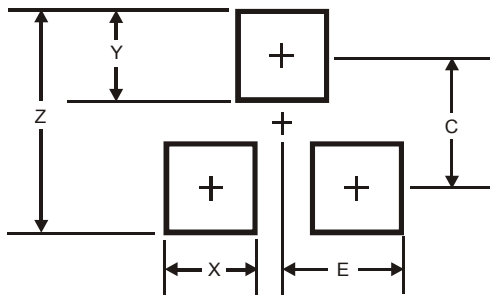
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



| SOT23                |       |      |       |
|----------------------|-------|------|-------|
| Dim                  | Min   | Max  | Typ   |
| A                    | 0.37  | 0.51 | 0.40  |
| B                    | 1.20  | 1.40 | 1.30  |
| C                    | 2.30  | 2.50 | 2.40  |
| D                    | 0.89  | 1.03 | 0.915 |
| F                    | 0.45  | 0.60 | 0.535 |
| G                    | 1.78  | 2.05 | 1.83  |
| H                    | 2.80  | 3.00 | 2.90  |
| J                    | 0.013 | 0.10 | 0.05  |
| K                    | 0.903 | 1.10 | 1.00  |
| K1                   | -     | -    | 0.400 |
| L                    | 0.45  | 0.61 | 0.55  |
| M                    | 0.085 | 0.18 | 0.11  |
| α                    | 0°    | 8°   | -     |
| All Dimensions in mm |       |      |       |

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| Z          | 2.9           |
| X          | 0.8           |
| Y          | 0.9           |
| C          | 2.0           |
| E          | 1.35          |

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